

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

**Claim 1: (Currently Amended)**      A semiconductor device having an NMOS and a PMOS, comprising:

each gate electrode of said NMOS and PMOS containing a polycrystalline silicon film formed on a gate insulating film and a metallic nitride film formed on said polycrystalline silicon film;

said polycrystalline silicon film of said ~~NMOS~~ PMOS containing a p-type impurity;

said polycrystalline silicon film of said ~~PMOS~~ NMOS containing a p-type impurity and an n-type impurity; and

said n-type impurity contained in said polycrystalline silicon film of said NMOS being segregated to a side of an interface of said polycrystalline silicon film and said gate insulating film, and said p-type impurity contained in said NMOS being segregated to a side of an interface of said metallic nitride film and said polycrystalline silicon film.

**Claim 2: (Original)**      A semiconductor device as claimed in claim 1, wherein each gate electrode of said NMOS and PMOS contains a metallic film formed on said metallic nitride film.